

L Number	Hits	Search Text	DB	Time stamp
1	4666	(HF or hydrofluoric) and (nitric or "HNO.sub.3") and acetic	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:48
4	2230	(HF or hydrofluoric) same (nitric or "HNO.sub.3") same acetic	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:19
3	397	"semiconductor die" same etch\$5	USPAT; EPO; JPO; IBM_TDB	2003/01/20 07:28
6	500	"semiconductor die" same (thinned or thinning or thin)	USPAT; EPO; JPO; IBM_TDB	2003/01/20 07:28
8	19	("semiconductor die" same (thinned or thinning or thin)) and (HF or hydrofluoric) and (nitric or "HNO.sub.3")	USPAT; EPO; JPO; IBM_TDB	2003/01/20 07:29
2	632	(die or chip) same (thinned or thinning) same semiconductor	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:08
12	5461	(die or dice) same etch\$4	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:15
13	57	((die or dice) same etch\$4 ) and ((HF or hydrofluoric) and (nitric or "HNO.sub.3") and acetic )	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:09
14	2609	(die or dice) with etch\$4	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:16
15	2448	die with etch\$4	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:37
17	138	((HF or hydrofluoric) same (nitric or "HNO.sub.3") same acetic ) and die	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:24
19	794	die with (thinned or thinning )	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:38
20	196	die and (thin\$4 or etch\$4) and (HF or hydrofluoric) and (nitric or "HNO.sub.3") and acetic	USPAT; EPO; JPO; IBM_TDB	2003/01/20 08:48